

8-Bit Serial or Parallel - Input/Serial-Output Shift Register with Input Latch

High-Performance Silicon-Gate CMOS

MC74HC597A

The MC74HC597A is identical in pinout to the LS597. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of an 8-bit input latch which feeds parallel data to an 8-bit shift register. Data can also be loaded serially.

The HC597A is similar in function to the HC589A, which is a 3-state device.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 516 FETs or 129 Equivalent Gates
- These are Pb-Free Devices*





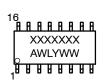


TSSOP-16 DT SUFFIX CASE 948F



QFN16 MN SUFFIX CASE 485AW

MARKING DIAGRAMS







A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

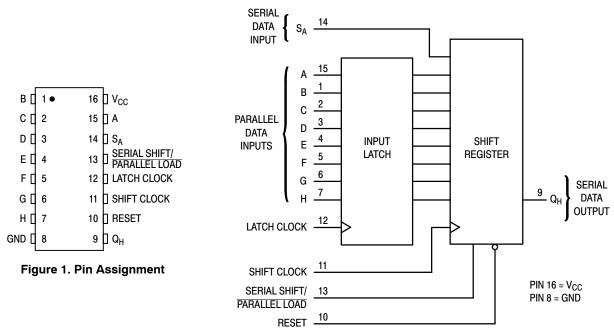


Figure 2. Logic Diagram

FUNCTION TABLE

			Input	S				on	
Operation	Re- set	Serial Shift/ Parallel Load	Latch Clock	Shift Clock	Serial Input S _A	Parallel Inputs A-H	Latch Contents	Shift Register Contents	Output Q _H
Reset shift register	L	Х	L, H, ∕	Х	Х	Х	U	L	L
Reset shift register; load parallel data into data latch	L	Х		Х	Х	a-h	a-h	L	L
Load parallel data into data latch	Н	Н		L,H, ∕_	Х	a-h	a-h	U	U
Transfer latch contents to shift register	Н	L	L, H, ∕_	Х	Х	Х	U	$LR_N \rightarrow SR_N$	LR _H
Contents of data latch and shift register are unchanged	Н	Н	L, H, ∕_	L,H,∕\	Х	Х	U	U	U
Load parallel data into data latch and shift register	Н	L		Х	Х	a-h	a-h	a-h	h
Shift serial data into shift register	Н	Н	Х		D	X	*	$SR_A = D;$ $SR_N \rightarrow SR_{N+1}$	$SR_G \rightarrow SR_H$
Load parallel data into data latch and shift serial data into shift register	Н	Н			D	a-h	a-h	$SR_A = D;$ $SR_N \rightarrow SR_{N+1}$	$SR_G \rightarrow SR_H$

LR = latch register contents SR = shift register contents

a-h = data at parallel data inputs A-H D = data (L, H) at serial data input S_A

U = remains unchanged X = don't care

^{* =} depends on latch clock input

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V	
V _{IN}	DC Input Voltage		-0.5 to V _{CC} + 0.5	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} + 0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±50	mA
I _{IK}	Input Clamp Current (V _{IN} < 0 or V _{IN} > V _{CC})	±20	mA	
I _{OK}	Output Clamp Current (V _{OUT} < 0 or V _{OUT} > V _{CC})		±20	mA
T _{STG}	Storage Temperature		-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		±150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 1)	SOIC-16 QFN16 TSSOP-16	126 118 159	°C/W
P _D	Power Dissipation in Still Air at 25°C	SOIC-16 QFN16 TSSOP-16	995 1062 787	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	– 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $ \begin{array}{c} V_{CC} = 2.0 \ V \\ V_{CC} = 3.0 \ V \\ V_{CC} = 4.5 \ V \\ V_{CC} = 6.0 \ V \\ \end{array} $	0 0 0 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

DC ELECTRICAL CHARACTERISTICS

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	–55 to 25°C	≤ 85 °C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4 4 5.9	1.9 4 4 5.9	V
		$\begin{array}{c c} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ I_{out} \leq 4.0 \text{ mA} \\ I_{out} \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{array}{c c} V_{in} = V_{IH} \text{ or } V_{IL} & \begin{array}{c} I_{out} \leq 2.4 \text{ mA} \\ I_{out} \leq 4.0 \text{ mA} \\ I_{out} \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

			Gu			
Symbol	Parameter	V _{CC} V	–55 to 25°C	≤85°C	≤125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle), Shift Clock (Figures 3 and 5)	2.0 3.0 4.5 6.0	10 15 30 50	9 14 28 45	8 12 25 40	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Latch Clock to Q _H (Figures 3 and 4)	2.0 3.0 4.5 6.0	175 100 40 30	225 110 50 40	275 125 60 50	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Shift Clock to Q _H (Figures 3 and 5)	2.0 3.0 4.5 6.0	160 90 30 25	200 130 40 30	240 160 48 40	ns
t _{PHL}	Maximum Propagation Delay, Reset to Q _H (Figures 3 and 6)	2.0 3.0 4.5 6.0	160 90 30 25	200 130 40 30	240 160 48 40	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Serial Shift/Parallel Load to Q _H (Figures 3 and 7)	2.0 3.0 4.5 6.0	160 90 30 25	200 130 40 30	240 160 48 40	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	40	pF

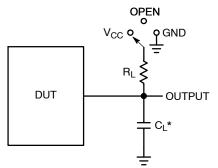
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$.

TIMING REQUIREMENTS

			Guaranteed Limit			
Symbol	Parameter	V _{CC} V	–55 to 25°C	≤ 85 °C	≤125°C	Unit
t _{su}	Minimum Setup Time, Parallel Data inputs A-H to Latch Clock (Figure 8)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _{su}	Minimum Setup Time, Serial Data Input S _A to Shift Clock (Figure 9)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _{su}	Minimum Setup Time, Serial Shift/Parallel Load to Shift Clock (Figure 10)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _h	Minimum Hold Time, Latch Clock to Parallel Data Inputs A-H (Figure 8)	2.0 3.0 4.5 6.0	15 10 2 2	20 15 3 3	30 25 5 4	ns
t _h	Minimum Hold Time, Shift Clock to Serial Data Input S _A (Figure 9)	2.0 3.0 4.5 6.0	2 2 2 2	2 2 2 2	2 2 2 2	ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Shift Clock (Figure 6)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _w	Minimum Pulse Width, Latch Clock and Shift Clock (Figures 4 and 5)	2.0 3.0 4.5 6.0	60 35 12 10	70 40 15 13	80 45 19 16	ns
t _w	Minimum Pulse Width, Reset (Figure 6)	2.0 3.0 4.5 6.0	60 35 12 10	70 40 15 13	80 45 19 16	ns
t _w	Minimum Pulse Width, Serial Shift/Parallel Load (Figure 7)	2.0 3.0 4.5 6.0	60 35 12 10	70 40 15 13	80 45 19 16	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 4)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

^{*}Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS



Test	Switch Position	CL	R _L
t _{PLH} / t _{PHL}	LH / t _{PHL} Open		1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}		
t _{PHZ} / t _{PZH}	GND		

*C_L Includes probe and jig capacitance

Figure 3. Test Circuit

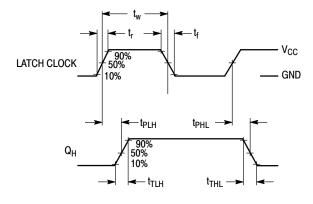


Figure 4. (Serial Shift/Parallel Load = L)

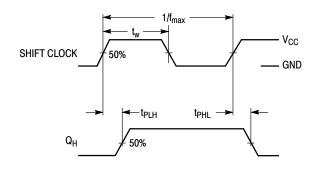
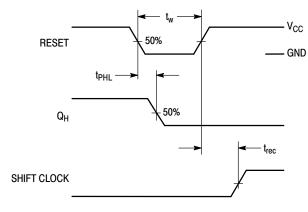


Figure 5. (Serial Shift/Parallel Load = H)



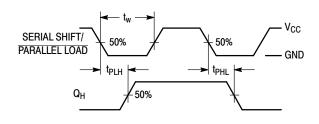
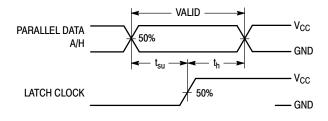


Figure 6.

Figure 7.



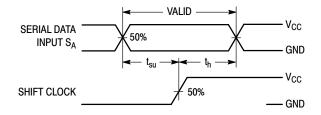


Figure 8.

Figure 9.

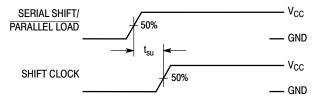


Figure 10.

PIN DESCRIPTIONS

DATA INPUTS

A, B, C, D, E, F, G, H (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Parallel data inputs. Data on these inputs is stored in the input latch on the rising edge of the Latch Clock input.

S_A (Pin 14)

Serial data input. Data on this input is shifted into the shift register on the rising edge of the Shift Clock input it Serial Shift/Parallel Load is high. Data on this input is ignored when Serial Shift/Parallel Load is low.

CONTROL INPUTS

Serial Shift/Parallel Load (Pin 13)

Shift register mode control. When a high level is applied to this pin, the shift register is allowed to serially shift data. When a low level is applied to this pin, the shift register accepts parallel data from the input latch, and serial shifting is inhibited.

Reset (Pin 10)

Asynchronous, Active-low shift register reset. A low level applied to this input resets the shift register to a low level, but does not change the data in the input latch.

Shift Clock (Pin 11)

Serial shift register clock. A low-to-high transition on this input shifts data on the Serial Data Input into the shift register and data in stage H is shifted out Q_H , being replaced by the data previously stored in stage G.

Latch Clock (Pin 12)

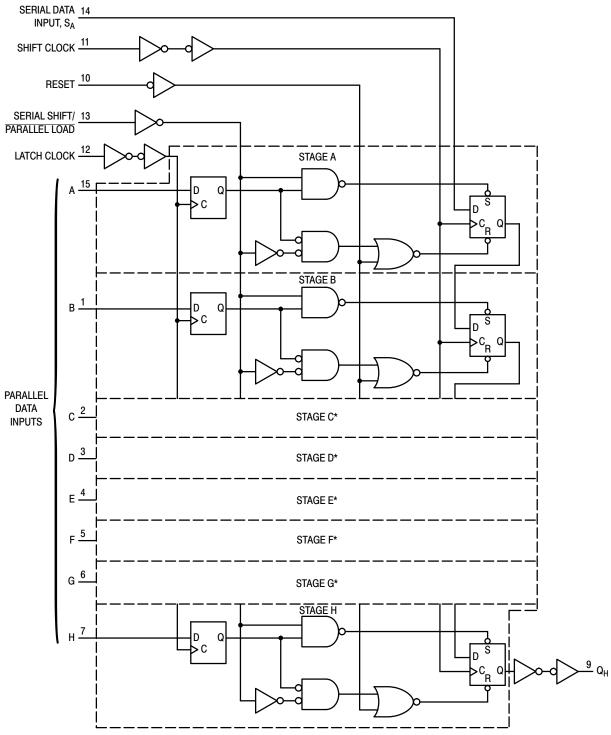
Latch clock. A low-to-high transition on this input loads the parallel data on inputs A–H into the input latch.

OUTPUT

Q_H (Pin 9)

Serial data output. This pin is the output from the last stage of the shift register.

EXPANDED LOGIC DIAGRAM



*NOTE: Stages C thru G (not shown in detail) are identical to stages A and B above.

Figure 11. Extended Logic Diagram

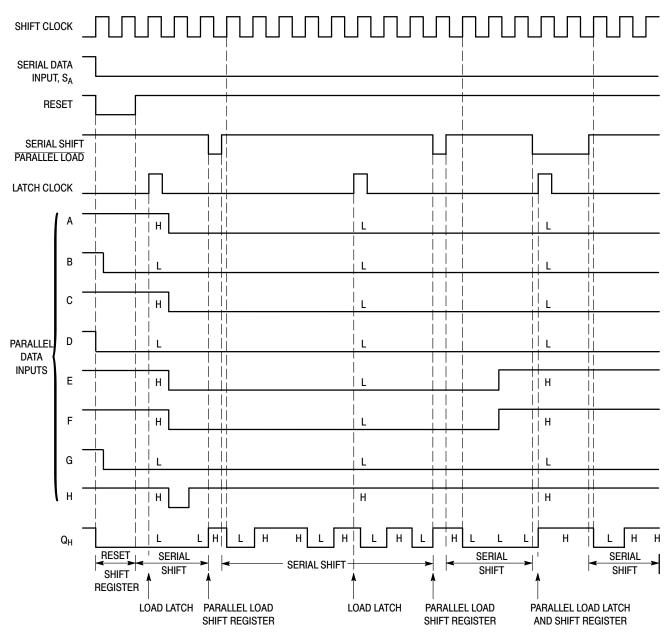


Figure 12. Timing Diagram

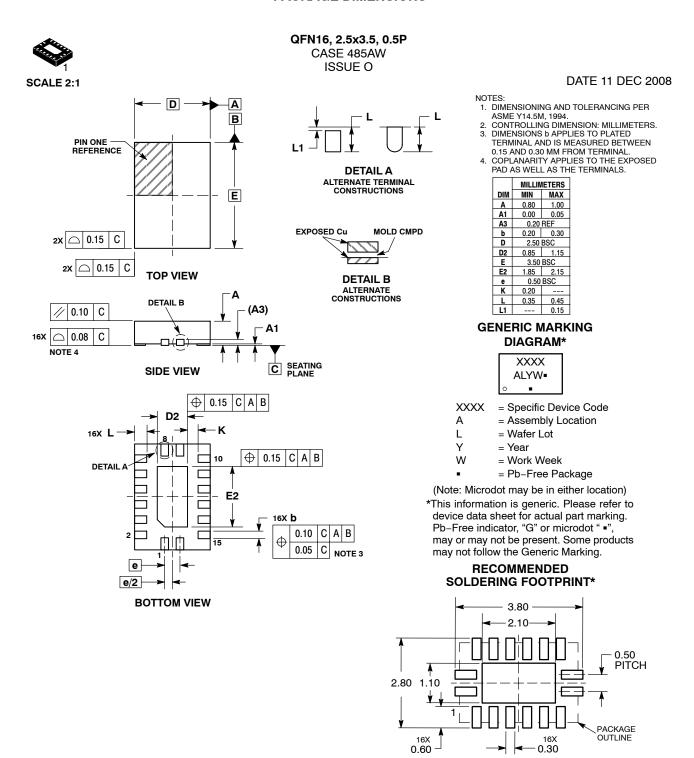
ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74HC597ADG	HC597AG	SOIC-16	48 Units / Rail
MC74HC597ADR2G	HC597AG	SOIC-16	2500 Units / Tape & Reel
MC74HC597ADTR2G	HC 597A	TSSOP-16	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*-}Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

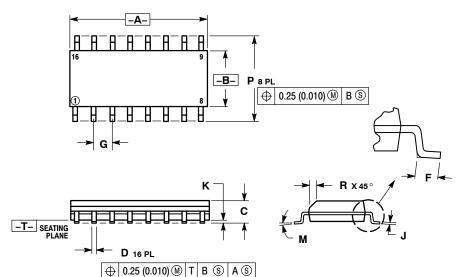
DIMENSIONS: MILLIMETERS





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.
- PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION.
 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		
PIN 1.	COLLECTOR		CATHODE		COLLECTOR, DYE #1		COLLECTOR, DYE #1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3	
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4	
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4	
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4	
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4	
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3	
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3	D=0014454D=D
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2	RECOMMENDED
14.	COLLECTOR			14.	BASE, #4	14.		SOLDERING FOOTPRINT*
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	00101111111
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8X
								← 6.40 →
STYLE 5:		STYLE 6:		STYLE 7:				
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH			16X 1.12 < ➤
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT	П		<u> </u>
3.	DRAIN, #2		CATHODE	3.	COMMON DRAIN (OUTPUT		1	1 16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,	*	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	Г)		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		16X	— —
7.	DRAIN, #4	7.		7.			0.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,	0.00	
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH			
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	Γ)	_	<u> </u>
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT	r)		
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	Γ)		
13.	GATE, #2	13.	ANODE	13.	GATE N-CH			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	Γ)		
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	Γ)		PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			
								□ 8 9 1 1 7
								1
								DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOIC-16		PAGE 1 OF 1				

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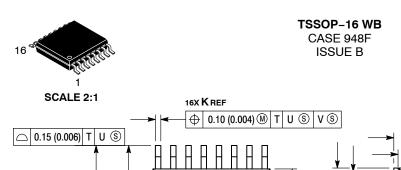
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☐ 0.15 (0.006)

PIN 1 IDENT.

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DATE 19 OCT 2006

NOTES

Κ

SECTION N-N

0.25 (0.010)

J1

В

-U-

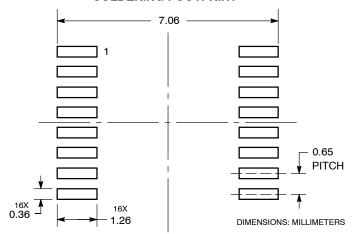
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	00	00	00	0 0

DETAIL E -W-☐ 0.10 (0.004) **DETAIL E** SEATING PLANE D

RECOMMENDED SOLDERING FOOTPRINT*

-V-



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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